62. A method for dynamic correction of scanning energy in the projection exposure system of claim 59, comprising the steps of:

measuring a distribution of scanning energy $SE_{wafer}(x_{wafer})$ in said second imaging plane;

comparing said measured distribution of scanning energy $SE_{wafer}(x_{wafer})$ to a predetermined distribution of scanning energy $SE_{Standard}(x_{wafer})$;

controlling an actuator to modify said field lens group to minimize a difference between said measured distribution of scanning energy $SE_{wafer}(x_{wafer})$ and said predetermined distribution of scanning energy $SE_{Standard}(x_{wafer})$.

63. A method of producing microstructured devices by lithography, comprising the step of using the projection exposure apparatus of claim 59.--

REMARKS

New claims 31 through 63 are added to protect properly the full scope of the invention.

Respectfully submitted,

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